

**WHAT IS CLAIMED IS:**

1. A magnetic random access memory device, comprising:

5 an array of magnetic elements;

a plurality of conductive lines configured to set magnetization states of the  
magnetic elements; and

10 circuitry configured to vary current applications along one or more of the  
conductive lines.

2. The magnetic random access memory device of claim 1, wherein the circuitry is  
configured to vary an amount of current applied to the one or more conductive lines.

15 3. The magnetic random access memory device of claim 2, wherein the circuitry is  
configured to vary the amount of current with respect to the direction along which the  
current is applied.

20 4. The magnetic random access memory device of claim 2, wherein the circuitry is  
configured to vary the amount of current with respect to the temperature of the magnetic  
random access memory device.

25 5. The magnetic random access memory device of claim 1, wherein the circuitry is  
configured to vary the point in time at which current is applied to the one or more  
conductive lines.

6. The magnetic random access memory device of claim 1, wherein the circuitry is  
configured to vary a length of time current is applied to the one or more conductive lines.

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7. The magnetic random access memory device of claim 6, wherein the circuitry is configured to apply a write pulse current along one or more of the conductive lines for a length of time sufficient to allow a source current to be measured from a voltage power supply coupled to the magnetic random access memory device during the application of  
5 the write pulse current.

8. The magnetic random access memory device of claim 1, wherein the circuitry is configured to vary current applications for write operations of the magnetic random access memory device.

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9. The magnetic random access memory device of claim 1, wherein the circuitry is configured to vary current applications for read operations of the magnetic random access memory device.

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10. The magnetic random access memory device of claim 9, wherein the circuitry is configured to vary an amount of bias voltage applied along at least one of the plurality of conductive lines.

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11. The magnetic random access memory device of claim 1, wherein the circuitry is configured to terminate the current applications upon determining a power level supplied to the magnetic random access memory device is below a predetermined threshold.

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12. The magnetic random access memory device of claim 1, further comprising a reprogrammable non-volatile latch configured to store parameter settings for the current applications.

13. A device, comprising:

a magnetic random access memory array; and

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a first storage circuit comprising one or more magnetic elements, wherein the first storage circuit is configured to store parameter settings characterizing operations of the magnetic random access memory array within the magnetic elements.

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14. The device of claim 13, wherein the parameter settings are settings selected for use by a customer of the device.

10 15. The device of claim 13, wherein the parameter settings are settings selected for testing qualitative features of the magnetic random access memory array.

16. The device of claim 13, further comprising an alternative means by which to store parameter settings characterizing operations of the magnetic random access memory array.

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17. The device of claim 16, further comprising a second storage circuit having one or more magnetic elements, wherein the second storage circuit is configured to send a control signal by which to select the first storage circuit or the alternative means to send the parameter settings to the magnetic random access memory array.

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18. The device of claim 13, further comprising circuitry configured to vary one or more values of the parameter settings during an operation of the magnetic random access memory array.

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19. A magnetic random access memory device, comprising:

an array of magnetic elements;

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a plurality of conductive lines configured to set magnetization states of the magnetic elements; and

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circuitry configured to terminate an application of current along one or more of  
the conductive lines before magnetization states of one or more magnetic  
elements selected for a write operation of the device are changed.

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20. The magnetic random access memory device of claim 19, wherein the circuitry is  
configured to:

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monitor a voltage level of a power supply coupled to the magnetic random access  
memory device; and

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terminate the application of current upon determining the voltage level is below a  
predetermined threshold.

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21. A method, comprising:

coupling a power source to a magnetic random access memory device;

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writing to at least one magnetic memory cell junction within the magnetic random  
access memory device;

monitoring current levels supplied from the power source; and

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determining a write pulse amplitude for the magnetic junction based on a  
difference between a current level measured during the step of writing and  
a current level measured not during the step of writing.

22. The method of claim 21, wherein the step of determining a write pulse amplitude for the magnetic junction comprises determining a difference between the current level measured during the step of writing and a current level measured prior to the step of writing.

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23. The method of claim 21, wherein the step of determining a write pulse amplitude for the magnetic junction comprises determining a difference between the current level measured during the step of writing and a current level measured subsequent to the step of writing.

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24. The method of claim 21, wherein the step of writing comprises:

raising a voltage application along an address path of the magnetic random access memory device to a level higher than a voltage of the power supply; and

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applying a current along a bit line coupled to the magnetic element for more than approximately 50 ns.

25. A method, comprising:

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applying an initial bias voltage on a magnetic element of a memory cell array;

altering the bias voltage incrementally;

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monitoring current levels associated with the initial bias voltage and the incremental bias voltages;

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determining a difference in current levels between the initial bias voltage and an incremental bias voltage associated with a level of current corresponding to a midpoint between two logic states of the magnetic element; and

classifying the magnetic element as unsatisfactory upon determining the difference is less than a predetermined level.

5 26. The method of claim 25, wherein the step of altering the bias voltage incrementally comprises increasing the bias voltage.

27. The method of claim 25, wherein the step of altering the bias voltage incrementally comprises decreasing the bias voltage.